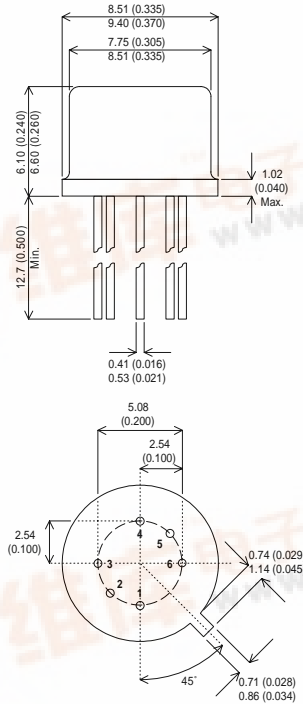


BFY84

MECHANICAL DATA

Dimensions in mm (inches)



TO77

- Pin 1 – Collector 1
- Pin 2 – Base 1
- Pin 3 – Emitter 1
- Pin 4 – Emitter 2
- Pin 5 – Base 2
- Pin 6 – Collector 2

SILICON PLANAR EPITAXIAL NPN TRANSISTOR

DESCRIPTION

The BFY84 is a six terminal device containing two isolated silicon planar epitaxial NPN transistors in Jedec TO77 metal case. The good thermal tracking over a wide current and temperature range, offers the circuit designer matched transistors with specified performance for differential amplifiers.

ABSOLUTE MAXIMUM RATINGS

V_{CBO}	Collector – Base Voltage ($I_E = 0$)	30V
V_{CEO}	Collector – Emitter Voltage ($I_B = 0$)	12V
V_{EBO}	Emitter – Base Voltage ($I_C = 0$)	3V
I_C	Collector Current	200mA
P_{tot}	Total Dissipation at $T_{amb} \leq 25^\circ C$ (one side)	0.3W
	$T_{amb} \leq 25^\circ C$ (both sides)	0.38W
	$T_{case} \leq 25^\circ C$ (one side)	0.6W
	$T_{case} \leq 25^\circ C$ (both sides)	0.98W
	$T_{case} \leq 100^\circ C$ (one side)	0.34W
	$T_{case} \leq 100^\circ C$ (both sides)	0.56W
	Storage and Junction Temperature	-65 to +200°C



THERMAL DATA

			One side	Both Sides	
$R_{thj-case}$	Thermal Resistance Junction-case	Max	292	178	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	583	460	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut Off Current $V_{CB} = 15V$ $I_E = 0$ $V_{CB} = 15V$ $T_{amb} = 150^{\circ}C$			10	nA
				1	μA
$V_{(BR)CBO}$	Collector Base Breakdown Voltage $I_C = 1\mu A$ $I_E = 0$	30			V
$V_{CEO(sus)*}$	Collector Emitter Sustaining Voltage $I_C = 3mA$ $I_B = 0$	12			V
$V_{(BR)EBO}$	Emitter Base Breakdown Voltage $I_C = 0$ $I_E = 10\mu A$	3			V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage $I_C = 10mA$ $I_B = 1mA$			0.4	V
$V_{BE(sat)}$	Base Emitter Saturation Voltage $I_C = 10mA$ $I_B = 1mA$			1	V
$ V_{BE1} - V_{BE2} $	Input Offset Voltage $I_C = 3mA$ $V_{CE} = 1V$			15	mV
$\frac{ V_{BE1} - V_{BE2} }{\Delta T}$	Input Offset Voltage Temperature Coefficient $I_C = 3mA$ $V_{CE} = 1V$			25	$\mu V/^{\circ}C$
h_{FE}	DC Current Gain $I_C = 3mA$ $V_{CE} = 1V$	20			—
h_{FE1}/h_{FE2}	Matched Pair Ratio $I_C = 3mA$ $V_{CE} = 1V$			1.25	
f_T	Transistion Frequency $I_C = 4mA$ $V_{CE} = 10v$ $f = 100MHz$	600			MHz
C_{EBO}	Emitter Base Capacitance $I_C = 0$ $V_{EB} = 0.5V$ $f = 1MHz$			2	pF
C_{CBO}	Collector Base Capacitance $I_E = 0$ $V_{CB} = -10V$ $f = 1MHz$			1.7	pF
NF	Noise Figure $I_C = 1mA$ $V_{CE} = 6V$ $f = 60MHz$			6	dB

* Pulse test $t_p = 300\mu s$, Duty Cycle = 1%